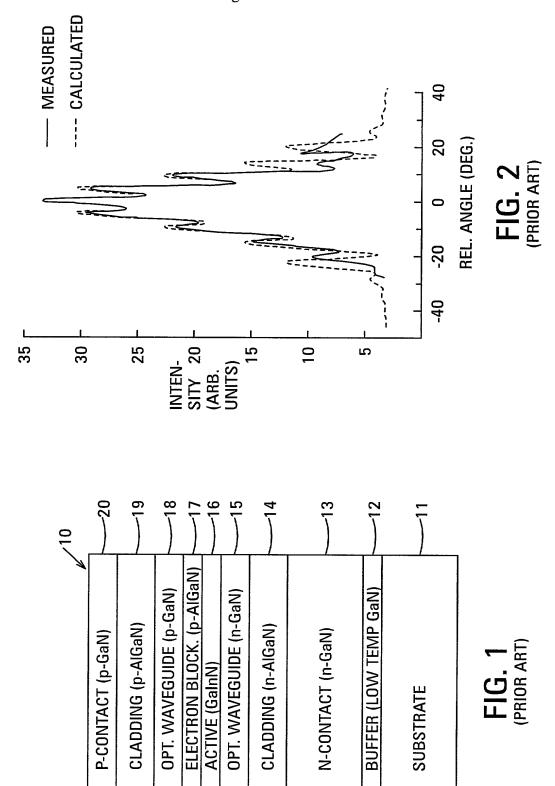
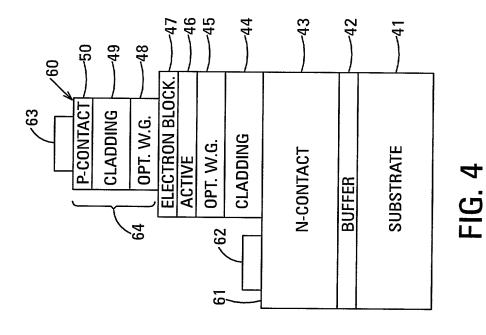
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P-CONTACT (GaN)

CLADDING (p-AIGaN)

ELECTRON BLOCK. (p-AIGaN)

ACTIVE (GaINN)

ACTIVE (AIGAN (HIGH AIN FRACTION))

BUFFER (LOWY TEMIP AIGAN)

ACTIVE (AIGAN (LOWY TEMIP AIGAN)

ACTIVE (AIGAN

F1G.

Inventors: Tetsuya Takeuchi et al. Agilent Docket No. 10991002-4 Page 3 of 4 **FIG.6** FIG.7 500 400 5. 300 CURRENT(mA) 0.5 1.0 CURRENT (A) 100 0 VOLT- 20 AGE DROP 15 (V) INTEN-SITY (ARB. UNITS) 30 10 30 25 വ --- CALCULATED MEASURED 40 20 REL. ANGLE (DEG.) INTEN-SITY (ARB. UNITS) 35 30 25 15 10 2

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